

# NTMD6P02, NVMD6P02

## Power MOSFET

6 A, 20 V, P-Channel SOIC-8, Dual

### Features

- Ultra Low  $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Logic Level Gate Drive
- Miniature Dual SOIC-8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Avalanche Energy Specified
- These Devices are Pb-Free and are RoHS Compliant
- NVMD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

### Applications

- Power Management in Portable and Battery-Powered Products, i.e.: Cellular and Cordless Telephones, and PCMCIA Cards

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-20	V
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 12$	V
Thermal Resistance – Junction-to-Ambient (Note 1) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 70^\circ\text{C}$ Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	$R_{\theta JA}$ $P_D$ $I_D$ $I_D$ $P_D$ $I_D$ $I_{DM}$	62.5 2.0 -7.8 -5.7 0.5 -3.89 -40	$^\circ\text{C/W}$ W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 2) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 70^\circ\text{C}$ Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	$R_{\theta JA}$ $P_D$ $I_D$ $I_D$ $P_D$ $I_D$ $I_{DM}$	98 1.28 -6.2 -4.6 0.3 -3.01 -35	$^\circ\text{C/W}$ W A A W A A
Thermal Resistance – Junction-to-Ambient (Note 3) Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 25^\circ\text{C}$ Continuous Drain Current @ $T_A = 70^\circ\text{C}$ Maximum Operating Power Dissipation Maximum Operating Drain Current Pulsed Drain Current (Note 4)	$R_{\theta JA}$ $P_D$ $I_D$ $I_D$ $P_D$ $I_D$ $I_{DM}$	166 0.75 -4.8 -3.5 0.2 -2.48 -30	$^\circ\text{C/W}$ W A A W A A
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ( $V_{DD} = -20$ Vdc, $V_{GS} = -5.0$ Vdc, Peak $I_L = -5.0$ Apk, $L = 40$ mH, $R_G = 25$ $\Omega$ )	$E_{AS}$	500	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

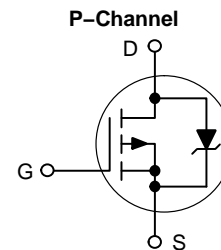
1. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided),  $t = 10$  seconds.
2. Mounted onto a 2" square FR-4 Board (1 in sq, 2 oz. Cu 0.06" thick single sided),  $t =$  steady state.
3. Minimum FR-4 or G-10 PCB,  $t =$  steady state.
4. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle = 2%.



ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

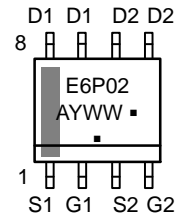
6 AMPERES, 20 VOLTS



### MARKING DIAGRAM & PIN ASSIGNMENT



SOIC-8  
CASE 751  
STYLE 11



E6P02 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NVMD6P02R2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

# NTMD6P02, NVMD6P02

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)\*

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = -250 μAdc) Temperature Coefficient (Positive)	V <sub>(BR)DSS</sub>	-20 -	- -11.6	- -	Vdc mV/°C
Zero Gate Voltage Drain Current (V <sub>DS</sub> = -20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 25°C) (V <sub>DS</sub> = -20 Vdc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 70°C)	I <sub>DSS</sub>	- -	- -	-1.0 -5.0	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> = -12 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	-100	nAdc
Gate-Body Leakage Current (V <sub>GS</sub> = +12 Vdc, V <sub>DS</sub> = 0 Vdc)	I <sub>GSS</sub>	-	-	100	nAdc

### ON CHARACTERISTICS

Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μAdc) Temperature Coefficient (Negative)	V <sub>GS(th)</sub>	-0.6 -	-0.88 2.6	-1.20 -	Vdc mV/°C
Static Drain-to-Source On-State Resistance (V <sub>GS</sub> = -4.5 Vdc, I <sub>D</sub> = -6.2 Adc) (V <sub>GS</sub> = -2.5 Vdc, I <sub>D</sub> = -5.0 Adc) (V <sub>GS</sub> = -2.5 Vdc, I <sub>D</sub> = -3.1 Adc)	R <sub>DS(on)</sub>	- - -	0.027 0.038 0.038	0.033 0.050 -	Ω
Forward Transconductance (V <sub>DS</sub> = -10 Vdc, I <sub>D</sub> = -6.2 Adc)	g <sub>FS</sub>	-	15	-	Mhos

### DYNAMIC CHARACTERISTICS

Input Capacitance	(V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>ISS</sub>	-	1380	1700	pF
Output Capacitance		C <sub>OSS</sub>	-	515	775	
Reverse Transfer Capacitance		C <sub>RSS</sub>	-	250	450	

### SWITCHING CHARACTERISTICS (Notes 5 and 6)

Turn-On Delay Time	(V <sub>DD</sub> = -10 Vdc, I <sub>D</sub> = -1.0 Adc, V <sub>GS</sub> = -10 Vdc, R <sub>G</sub> = 6.0 Ω)	t <sub>d(on)</sub>	-	15	25	ns
Rise Time		t <sub>r</sub>	-	20	50	
Turn-Off Delay Time		t <sub>d(off)</sub>	-	85	125	
Fall Time		t <sub>f</sub>	-	50	110	
Turn-On Delay Time	(V <sub>DD</sub> = -16 Vdc, I <sub>D</sub> = -6.2 Adc, V <sub>GS</sub> = -4.5 Vdc, R <sub>G</sub> = 6.0 Ω)	t <sub>d(on)</sub>	-	17	-	ns
Rise Time		t <sub>r</sub>	-	65	-	
Turn-Off Delay Time		t <sub>d(off)</sub>	-	50	-	
Fall Time		t <sub>f</sub>	-	80	-	
Total Gate Charge	(V <sub>DS</sub> = -16 Vdc, V <sub>GS</sub> = -4.5 Vdc, I <sub>D</sub> = -6.2 Adc)	Q <sub>tot</sub>	-	20	35	nC
Gate-Source Charge		Q <sub>gs</sub>	-	4.0	-	
Gate-Drain Charge		Q <sub>gd</sub>	-	8.0	-	

### BODY-DRAIN DIODE RATINGS (Note 5)

Diode Forward On-Voltage	(I <sub>S</sub> = -1.7 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = -1.7 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	- -	-0.80 -0.65	-1.2 -	Vdc
Diode Forward On-Voltage	(I <sub>S</sub> = -6.2 Adc, V <sub>GS</sub> = 0 Vdc) (I <sub>S</sub> = -6.2 Adc, V <sub>GS</sub> = 0 Vdc, T <sub>J</sub> = 125°C)	V <sub>SD</sub>	- -	-0.95 -0.80	- -	Vdc
Reverse Recovery Time	(I <sub>S</sub> = -1.7 Adc, V <sub>GS</sub> = 0 Vdc, dI <sub>S</sub> /dt = 100 A/μs)	t <sub>rr</sub>	-	50	80	ns
		t <sub>a</sub>	-	20	-	
		t <sub>r</sub>	-	30	-	
Reverse Recovery Stored Charge		Q <sub>RR</sub>	-	0.04	-	μC

5. Indicates Pulse Test: Pulse Width = 300 μs max, Duty Cycle = 2%.

6. Switching characteristics are independent of operating junction temperature.

\*Handling precautions to protect against electrostatic discharge are mandatory.

# NTMD6P02, NVMD6P02

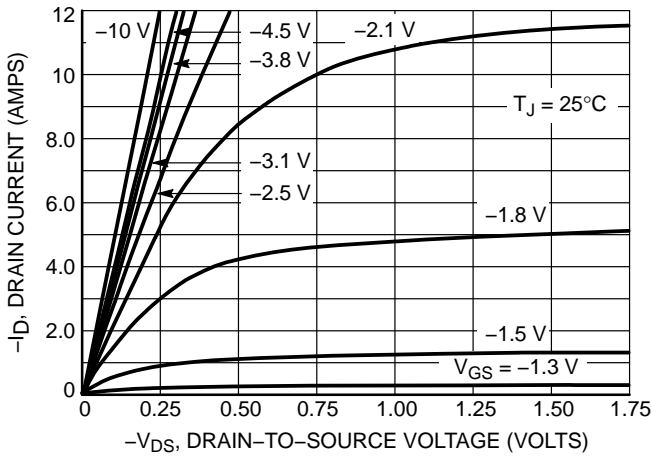


Figure 1. On-Region Characteristics

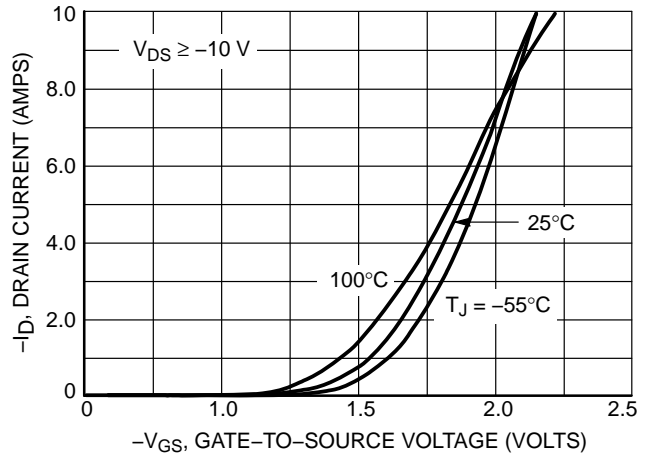


Figure 2. Transfer Characteristics

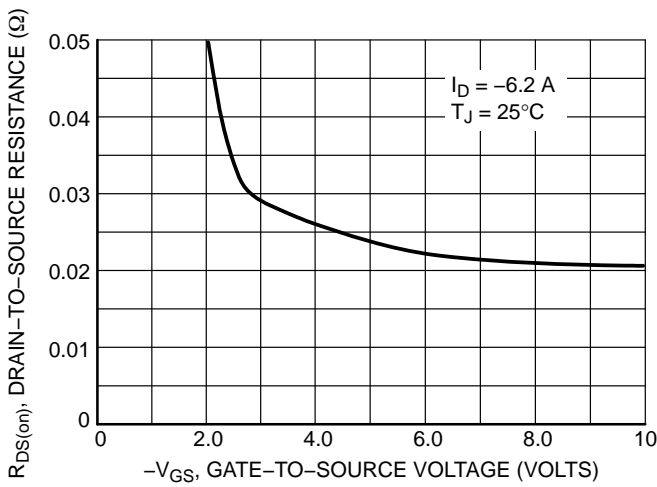


Figure 3. On-Resistance versus Gate-To-Source Voltage

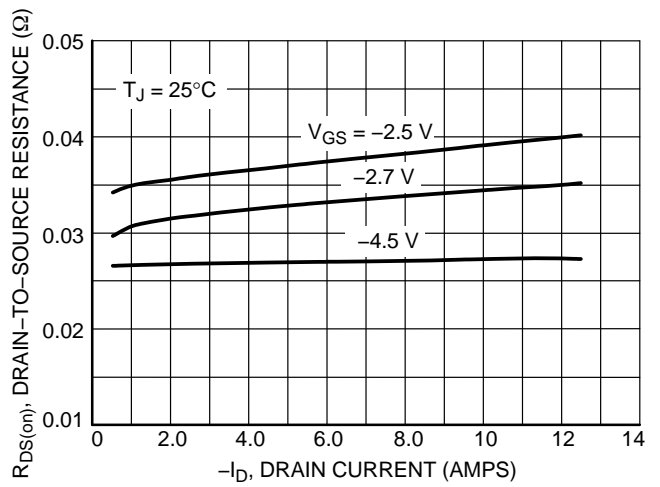


Figure 4. On-Resistance versus Drain Current and Gate Voltage

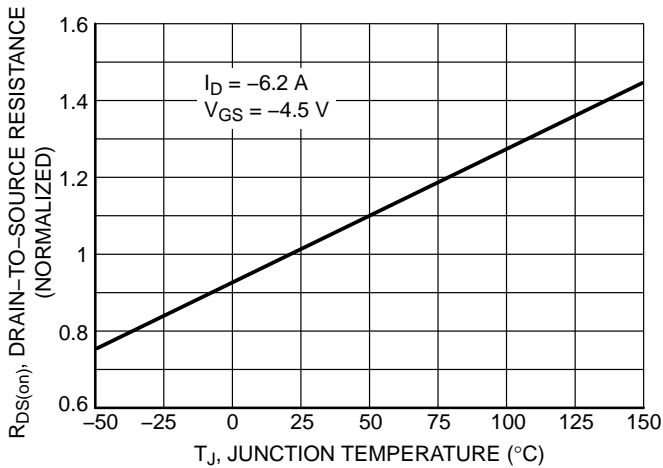


Figure 5. On-Resistance Variation with Temperature

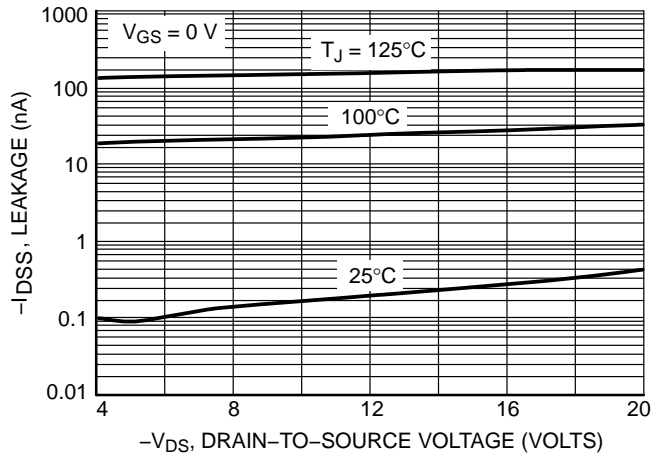
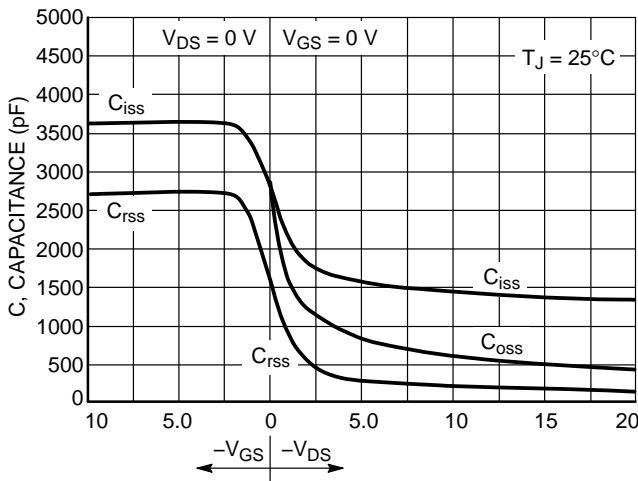
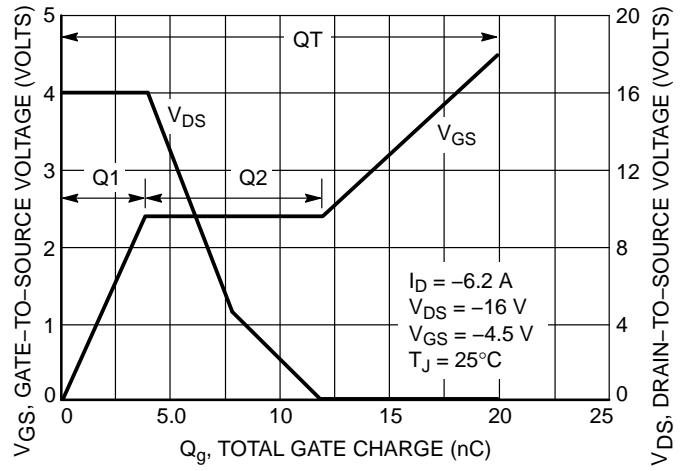


Figure 6. Drain-To-Source Leakage Current versus Voltage

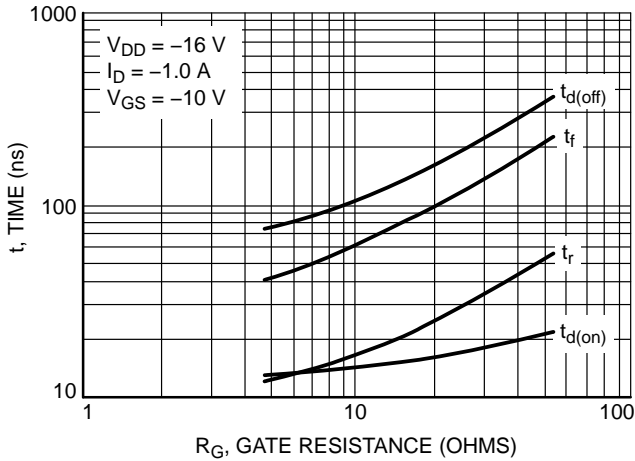
# NTMD6P02, NVMD6P02



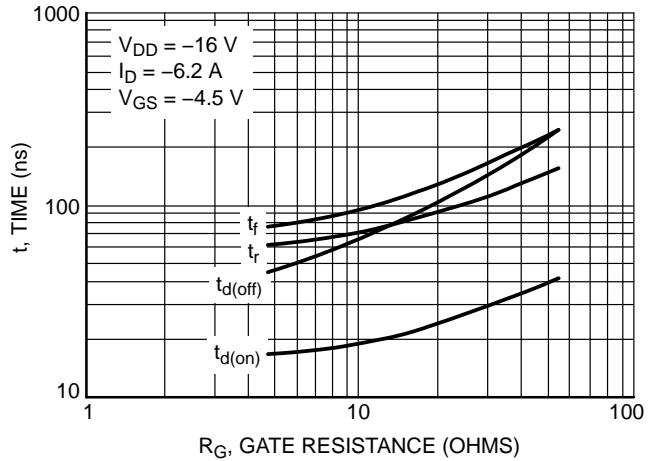
GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)  
**Figure 7. Capacitance Variation**



**Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge**

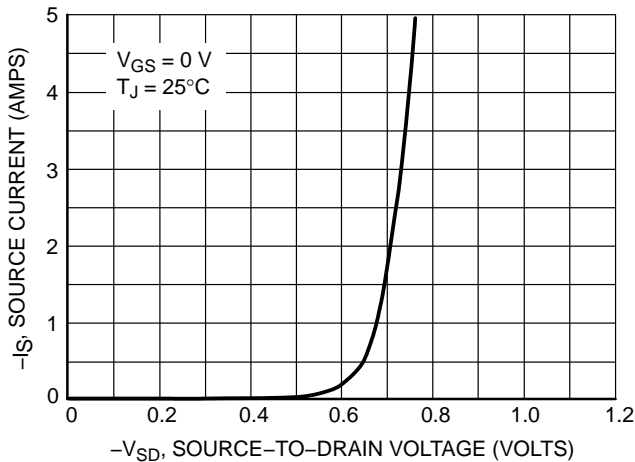


**Figure 9. Resistive Switching Time Variation versus Gate Resistance**

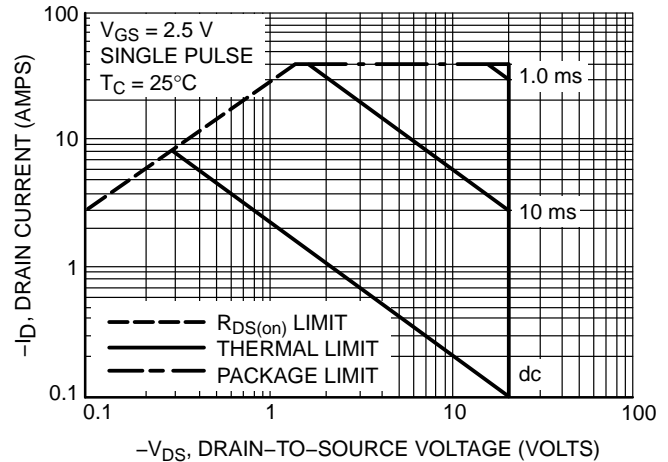


**Figure 10. Resistive Switching Time Variation versus Gate Resistance**

## DRAIN-TO-SOURCE DIODE CHARACTERISTICS



**Figure 11. Diode Forward Voltage versus Current**



**Figure 12. Maximum Rated Forward Biased Safe Operating Area**

# NTMD6P02, NVMD6P02

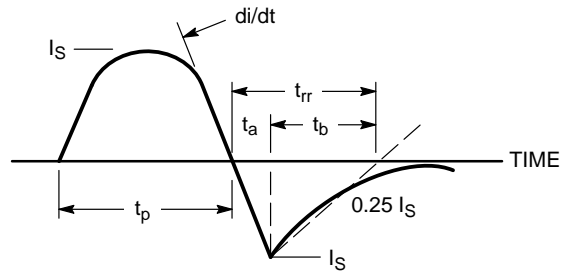


Figure 13. Diode Reverse Recovery Waveform

## TYPICAL ELECTRICAL CHARACTERISTICS

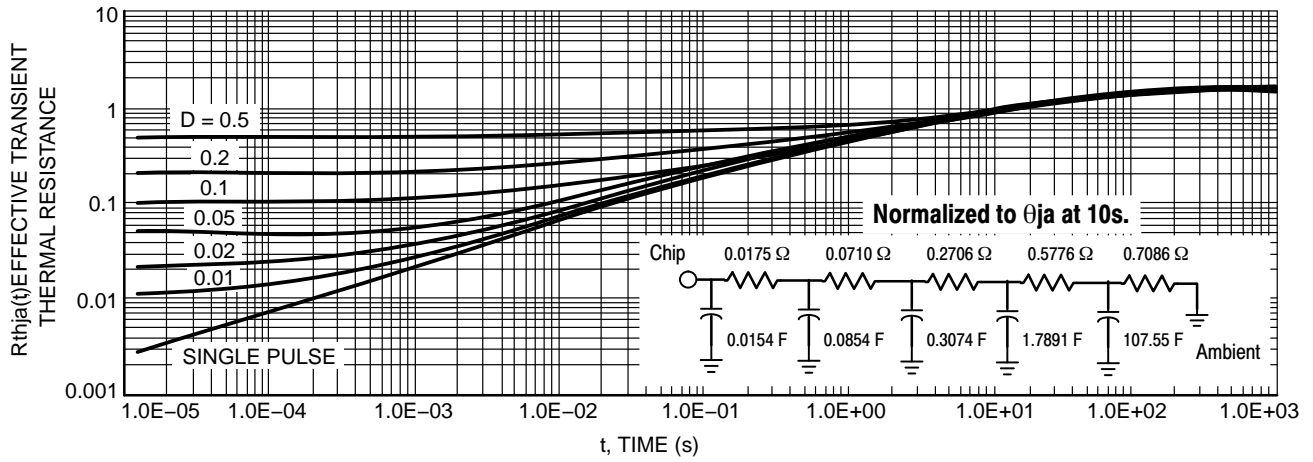


Figure 14. Thermal Response

